

## 1N4001F THRU 1N4007F

DESCRIPTION

Cathode

Anode

PINNING

PIN

1

2

### **Surface Mount General Purpose Silicon Rectifiers**

Reverse Voltage - 50 to 1000 V Forward Current - 1 A

#### **FEATURES**

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Juntion
- Easy to pick and place
- Lead free in comply with EU RoHS 2011/65/EU directives

#### **MECHANICAL DATA**

• Case: SMAF

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 27mg 0.00086oz

### **Maximum Ratings and Electrical characteristics**

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

	1 2				
1/65/EU directives					
	Top View				
	Simplified outline SMAF and symbol				
0, Method 2026					

Parameter	Symbols	1N4001F	1N4002F	1N4003F	1 N4004F	1N4005F	1N4006F	1N4007F	Units
Maximum Repetitive Peak Reverse Voltage	V <sub>rrm</sub>	50	100	200	400	600	800	1000	٧
Maximum RMS voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	٧
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta = 65 °C	I <sub>F(AV)</sub>	1						Α	
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>	30						Α	
Maximum Instantaneous Forward Voltage at 1 A	V <sub>F</sub>	1.1					V		
Maximum DC Reverse Current Ta = 25 °C at Rated DC Blocking Voltage Ta = 125 °C	I <sub>R</sub>	5 50					μA		
Typical Junction Capacitance 1>	C <sub>j</sub>	9					рF		
Typical Thermal Resistance <sup>2)</sup>	R <sub>sJA</sub>	115					°C/W		
Operating and Storage Temperature Range	Tj, Tsig	-55 ~ +150						°C	

<sup>1 )</sup>Measured at 1 MHz and applied reverse voltage of 4 V D.C

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<sup>2)</sup> Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length, P.C.B. mounted



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Fig.1 Forward Current Derating Curve

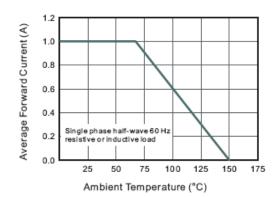


Fig.2 Typical Instaneous Reverse Characteristics

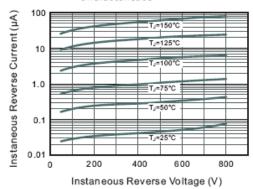


Fig.3 Typical Forward Characteristic

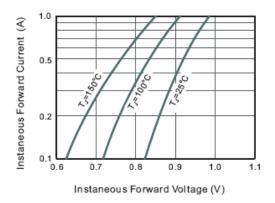
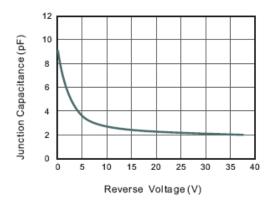


Fig.4 Typical Junction Capacitance



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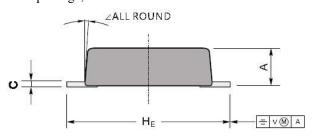


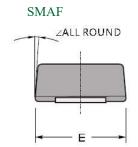


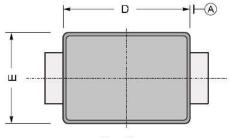
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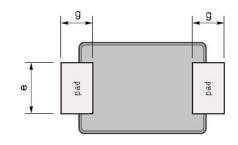
### PACKAGE OUTLINE

Plastic surface mounted package; 2 leads







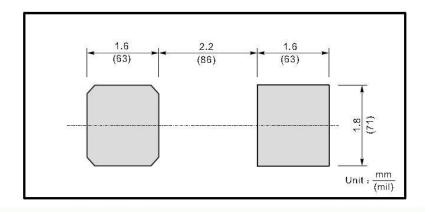


Top View

Bottom View

UNIT		Α	О	D	Ш	e	9	H∈	_
mm	max	1.1	0.20	3.7	2.7	1.6	1.2	4.9	
	min	0.9	0.12	3.3	2.4	1.3	0.8	4.4	7°
mil	max	43	7.9	146	106	63	47	193	<u>(</u>
	min	35	4.7	130	94	51	31	173	

### The recommended mounting pad size



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